June 1999



Si9936DY*

Dual N-Channel Enhancement Mode MOSFET

General Description

These N-Channel Enhancement Mode MOSFETs are produced using Fairchild Semiconductor's advance process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

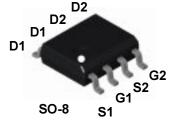
Applications

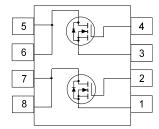
- · Battery switch
- Load switch
- Motor controls

Features

• 5.0 A, 30 V.
$$R_{DS(ON)} = 0.050 \ \Omega \ @V_{GS} = 10 \ V$$
 $R_{DS(ON)} = 0.080 \ \Omega \ @V_{GS} = 4.5 \ V$

- · Low gate charge.
- · Fast switching speed.
- · High power and current handling capability.





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		<u>+</u> 20	V
I _D	Drain Current - Continuous	(Note 1a)	5.0	Α
	- Pulsed		40	
P _D	Power Dissipation for Single Operation		2.0	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1	
		(Note 1c)	0.9	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	∘C

Thermal Characteristics

R _{eJA}	Thermal Resistance, Junction-to-Ambient		62.5	∘C/W
Rolc	Thermal Resistance, Junction-to-Case	(Note 1)	40	∘C/W

Package Outlines and Ordering Information

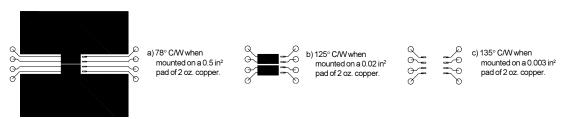
Device Marking	ce Marking Device		Tape Width	Quantity	
9936	SI9936DY	13"	12mm	2500 units	

^{*} Die and manufacturing source subject to change without prior notification.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30			٧
ΔBVDSS ΔTJ	Breakdown Voltage Temperature Coefficient	I _D = 250 _μ A,Referenced to 25°C		70		mV/∘C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55°C			2 20	μА
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Chara	cteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1			V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		-4.5		mV/∘C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}, T_J = 125 \circ \text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 3.9 \text{ A}$		0.044 0.066 0.066	0.050 0.100 0.080	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	40			Α
g _{FS}	Forward Transconductance	V _{DS} = 15 V, I _D = 5 A		8		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 15 V, V _{GS} = 0 V,		525		pF
Coss	Output Capacitance	f = 1.0 MHz		315		pF
C _{rss}	Reverse Transfer Capacitance]		185		pF
Switching	Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 1 \text{ A}, R_L = 15 \Omega$		12	30	ns
t,	Turn-On Rise Time	$V_{GS} = 10 \text{ V, } R_{GEN} = 6 \Omega$		10	25	ns
t _{d(off)}	Turn-Off Delay Time	1		25	50	ns
t _f	Turn-Off Fall Time	1		10	50	ns
t _{rr}	Drain-Source Reverse Recovery Time	$I_F = 5 \text{ A, di/dt} = 100 \text{A/}_{\mu} \text{s}$			160	nS
Q _g	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_{D} = 5\text{A},$		17	35	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		1.5		nC
Q_{gd}	Gate-Drain Charge			3.7		nC
Drain-So	urce Diode Characteristic	s and Maximum Ratings				
I _s	Maximum Continuous Drain-So				1.7	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = 1.7 A$ (Note 2)		0.78	1.2	٧

Notes

1. $R_{\theta,JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta,JC}$ is guaranteed by design while $R_{\theta,JA}$ is determined by the user's board design.



Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%

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